Half-auxeticity and anisotropic transport in Pd decorated two-dimensional boron sheets

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ABSTRACT

If one strains a material along a direction, most materials shrink normal to that direction. Similarly, if you compress the material, it will expand in the direction orthogonal to the pressure. Few materials, those of negative Poisson ratio, show the opposite behavior. Here, we show an unprecedented feature, a material that expands normal to the direction of force regardless if it is strained or compressed. Such behavior, called half-auxeticity, has been found for a borophene sheet stabilized by decorating Pd atoms. Herein, we explore Pd-decorated borophene, identify three stable phases of which one has this peculiar property of half auxeticity. After carefully analyzing stability, mechanical and electronic properties we explore the origin of this very uncommon behavior.

KEYWORDS

two-dimensional materials, auxetic materials, borophene, buckling structure, first-principle calculations

INTRODUCTION

Among a number of synthetic two-dimensional (2D) flatlands, 2D boron-based materials have sparked great scientific interests in recent research^{1,2} due to their unique characteristics including structural polymorphism,³ optical transparency⁴ and versatile band structure features.^{5,6} However, the trivalent outer shell of boron cannot completely occupy the in-plane sp² bonding state, making their structures fluxional⁷ and the synthesis of 2D borophene extremely relies on the metal substrates to compensate the boron's electron-deficiency. To achieve free-standing boron sheets, embedding metal atoms that can donate electrons to the boron frameworks has been considered as an effective strategy. Consequently, some metal-boron monolayers including MgB₂,⁸ BeB₂,⁹ FeB₂,¹⁰ FeB₆,¹¹ MnB,¹² TiB₂¹³ and TiB₄¹⁴ have been designed and found to possess novel features including planar hypercoordination, Dirac cones and high Curie temperature.^{10,12,14} With many intriguing chemical and physical properties, new 2D metal-boron compounds are expected to have important application potential for nanomechanics and nanoelectronics.

2D materials usually demonstrate excellent mechanical properties, often superior than their three- dimensional (3D) counterparts.¹⁵ They are flexible and can sustain ultra-high critical strains. In recent years, 2D materials with negative Poisson's ratio (NPR) have drawn great attention due to their unconventional lattice response under compression or tension. ¹⁶⁻¹⁹ Poisson's ratio $v = -\varepsilon_{\text{trans}}/\varepsilon_{\text{axial}}$ is the negative ratio between the strain along the transverse direction $\varepsilon_{\text{trans}}$ in response to an applied uniaxial strain $\varepsilon_{\text{axial}}$. From the daily life experience, most materials would naturally contract in the transverse direction when it is stretched along the longitudinal direction, namely, they have a positive Poisson's ratio (PPR). In contrast, materials with NPR, also known as auxetic materials, would exhibit the rather counterintuitive behavior: they would expand (contract) laterally when a longitudinal tensile (compressive) strain applied. As a result, such materials typically have enhanced toughness, indentation resistance and shear resistance.²⁰ With these exotic properties, auxetic materials display great potentials in aerospace, biomedicine, military defense and electronics.²¹⁻²³ However, compared with 3D bulks, 2D auxetic materials are still rare. Currently, the reported 2D materials with NPR can be classified into three groups, i.e. in-plane NPR (the NPR exists in $\pm x$ or $\pm y$ or other directions within the plane, e.g. penta-graphene),²⁴ out-of-plane NPR (the NPR exists in $\pm z$ direction, e.g. black phosphorus)¹⁶ and bidirectional NPR (the NPR exists both in-plane and out-of-plane, e.g. Ag₂S, borophene).^{25,26} Considering their enhanced mechanical performances and fascinating applications, it is interesting to explore whether there would exist additional auxetic 2D materials, or even new auxeticity types within the class of 2D materials.

In this work, we perform a systematic structure search of palladium borides PdB_n (n=2,3,4)

sheets by using first-principles calculations combined with particle swarm optimization (PSO) algorithm^{27,28} (see the details in the SI) and revealed a novel NPR material with desirable mechanical and electronic properties. The 2D boron sheets were incorporated with Pd atoms because: It is a transition metal widely used in electronics (as electrodes)²⁹ and catalysis;³⁰ it can efficiently donate electrons to boron, and its 2D nanostructures are expected to be well stabilized in experiment;³¹ and it has the lowest melting point among the platinum group metals,³² which could facilitate the experimental synthesis. Finally, three low-energy Pd-B monolayers, one of PdB4, and two of PdB2 (PdB2-I and PdB2-II) stoichiometries, were discovered in this work. Importantly, the PdB4 monolayer displays a so-far undiscovered auxetic phenomenon: along one crystal axis, the Poisson's ratio is negative for tensile strains, but becomes positive for compressive strains. As the NPR here occurs only for half of the strain parameter range, we term the effect as "half auxeticity". To our knowledge, such phenomenon has not been reported before, and it renders PdB₄ as an attractive material with potential applications in nanomechanics. Although excellent electronic properties such as high carrier mobilities (~10³ $cm^2 \cdot s^{-1} \cdot V^{-1}$ for the semiconducting PdB₂-I sheet) or Dirac loop (for the metallic PdB₂-II sheet) can be found in the PdB₂ monolayers (Fig. 1b and 1c), they are excluded in the following discussion due to their less interesting PPR nature. Nonetheless, as these phases are both thermodynamically stable with formation energies of -105 and -3 meV/atom, respectively, and are very likely to occur when decorating borophene, we discuss their stabilities, structural, electronic and optical properties in detail in the supporting information (Fig. S1-S7).

RESULTS AND DISCUSSION

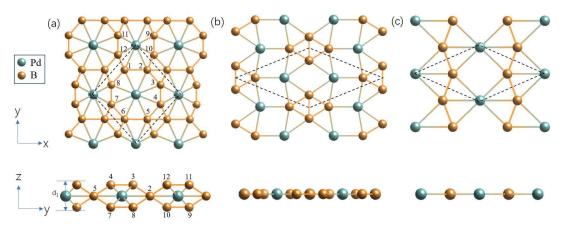


Figure 1. Top and side view of (a) PdB₄, (b) PdB₂-I (c) PdB₂-II monolayers. The dashed frame represents the primitive cell for each structure.

Structure of the PdB₄ monolayer. As shown in Fig. 1a, the B atoms in PdB₄ monolayer form a network composed of 4-membered and 8-membered rings, and more interestingly, each Pd atom is octacoordinated to B atoms, forming Pd-B₈ wheel-like structural motifs.

Such peculiar hypercoordinated structures with B have been attracting great interest for a long time, originally found in molecules/clusters³³⁻³⁶ and most recently extended to periodic 2D systems.^{11,14} The PdB₄ phase crystallizes in the C2/M space group with in-plane anisotropy. More importantly, the structure is not completely planar, but is corrugated with a thickness (d₁) of 1.61 Å. As indicated in Fig. 1a, in each unit cell, four out of the eight B atoms are moved out of the 2D plane formed by other atoms, two shifted above (atom 7, 8) and two shifted down (atom 3, 4). The corrugation significantly stabilizes the 2D sheet by 73.5 meV/atom, indicating the robustness of the buckled geometry. From the Bader charge analysis we find a sizable charge transfer from the Pd (0.22 e per atom) to boron atoms. According to the analysis by Pu et al., ³⁶ in a planar configuration, B₈ ring can only enclose smaller 3d elements, such as Mn, Fe, and Co. Pd is a 4d element with larger radius than 3d. Therefore, the observed buckling is consistent with the previous analysis, and is an intrinsic feature for the hypercoordinated Pd-B₈ wheel structure. As we shall see, the hypercoordination and the buckling play crucial roles in generating the half auxetic effect in PdB₄.

Stability of the PdB₄ **monolayer.** To access the experimental feasibility to grow the predicted PdB₄ layer, we first evaluated the thermodynamic stability by calculating the formation energy. We define the formation energy per atom E_f with respect to borophene and solid palladium: $E_f = [E(PdB_n) - xE(Pd) - yE(B)]/(x+y)$, where $E(PdB_4)$, E(Pd), and E(B) are the energy of the monolayer, the energy per atom of the solid Pd, and the energy of borophene monolayer,¹ respectively, thus to experimentally available phases of the constituting elements. The estimated E_f for PdB₄ is -42.0 meV/atom, indicating that it is a thermodynamically stable Pd-B phase, even more stable than aggregated Pd clusters at the borophene surface. Based on the elastic stability criteria³⁷, stable 2D lattices should satisfy: C_{11} , C_{22} , $C_{66} > 0 \& C_{11} + C_{22} - 2C_{12} > 0$, where C_{ij} are the elastic constants. This criterion is met here, see Table S1 for summarized values.

There are no imaginary frequencies in the phonon dispersion (Fig. S1a), which otherwise shows the typical behavior of a kinetically stable 2D material, with two linear and one parabolic acoustic branches. The highest frequencies of PdB₄ reach up to 1214 cm⁻¹ (36.4 THz), which is higher than the highest frequencies found in silicene (580 cm⁻¹),³⁸ Cu₂Si (420 cm⁻¹)³⁹, MoS₂ monolayers (473 cm⁻¹).⁴⁰. Such high-energy phonons characterize the robust Pd–B and B–B interactions in PdB₄. We further perform AIMD simulation at 300 K to evaluate the thermal stability of the PdB₄ sheet, in which a supercell containing 80 atoms was used. The snapshot taken at the end of 10 ps simulation is presented in Fig. S2a. We find the framework is well preserved as in the original configuration, indicating it is thermally stable.

Electronic properties of the PdB4 monolayer. PdB4 monolayer is a semiconductor with an

indirect gap of, at the HSE06 hybrid functional level, 1.22 eV. As shown in Fig. 2, the valence band maximum (VBM) for PdB₄ phase is along M- Γ line, while the conduction band minimum (CBM) locates at M point. From the projected density of states (PDOS), it can be found both VBM and CBM of PdB₄ and PdB₂ are contributed by the hybridized Pd-*d* and B-*p* states (Fig. 2b). The partial charge density distributions plotted in Fig. 2c-2d is in consistence with the PDOS results. The carrier (electron or hole) mobility of 2D materials has a great effect on the performance of electronic devices. We thus evaluated the charge transport of PdB₄ based on deformation potential (DP) theory. ⁴¹ The details for the carrier mobility (μ) results are provided in the SI (Fig. S8 and Table S2). For PdB₄ monolayer, the calculated electron (hole) mobility along y direction is 2270 (1640) $cm^2 \cdot s^{-1} \cdot V^{-1}$, which is much larger than that along x direction (960 (43) $cm^2 \cdot s^{-1} \cdot V^{-1}$). This indicates carrier transport is preferred along y direction. Notably, the carrier mobilities for PdB₄ are comparable to that in phosphorene ($\sim 10^4 \ cm^2 \cdot s^{-1} \cdot V^{-1}$)⁴³, demonstrating its excellent conductivity.

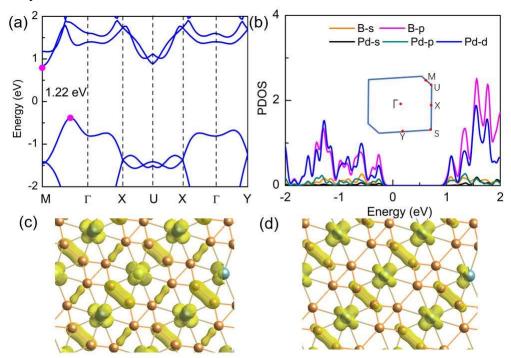


Figure 2. (a) Band structure and (b) PDOS for PdB_4 monolayer. Inset of (b): The Brillouin zone. (c-d) Partial charge density distributions of the VBM and CBM for PdB_4 monolayer. The isosurface is set to be 0.01 eÅ⁻³.

Strain effect of the PdB₄ monolayer. We then explore the strain effect on the electronic properties PdB₄ monolayer. In Fig. 3, we present the evolution of band edge levels and energy gaps under the strain along x direction. The uniaxial strain is defined as $\varepsilon_i = \frac{l_i - l_{i0}}{l_{i0}} \times 100\%$, where *i* represents a certain direction such as x, y or z. l_i and l_{i0} represent the

lattice constant under a certain strain and for a strain-free system, respectively. As the results for the y direction are similar (Fig. S9), they are therefore not displayed here. In the strain range from -6% to +6%, we find the position of CBM drops down to lower energy level when strain increases, while that of CBM shifts up towards the Fermi level. Consequently, the energy gap E_g decreases with the increased strain. To quantify the sensitivity of strain against E_g, we plot the rate of change of E_g (R(E_g))with respect to ε_x , which is defined as the change of bandgap over the change of strain, i.e. $\Delta E_g / \Delta \varepsilon_x$. Results show that in an experimentally available strain of 2%, the absolute value of R(E_g) researches up to ~110 meV/% strain, which is higher than that of single-layer transition metal dichalcogenides such as MoS₂ (45 meV/%)⁴⁴, WSe₂ (60-70 meV/%)⁴⁵ and MoSe₂ (27 meV/%)⁴⁶. The pronounced rate of change indicates electronic properties of PdB₄ monolayer is highly sensitive to the strain engineering and thus exhibits promising application in strain sensors.

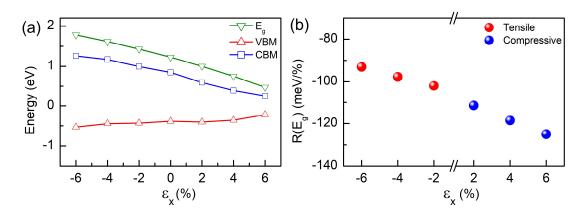


Figure 3. (a) Band edge positions and band gap (E_g) of PdB₄ monolayer under uniaxial strains x. (b) rate of change of bandgap $(R(E_g))$ as a function of uniaxial tensile/compressive strain.

Mechanical properties of the PdB4 monolayer. The unique geometries in the Pd-B8 wheels in PdB₄ sheet show fascinating mechanical performance, and it is thus intriguing to explore them in more detail. In the elastic theory, 2D Young's modulus along x and y direction is as $Y_r^{2D} = C_{11}C_{22} - C_{12}C_{21}/C_{22}$ $Y_{\nu}^{2D} =$ defined by elastic constants and $C_{11}C_{22} - C_{12}C_{21}/C_{11}$, respectively. The evaluated Y_x^{2D} and Y_y^{2D} are 105.7 and 121.4 GPa nm for PdB4, which is mechanically anisotropic. The values are about 32% - 47% of that in 2D MoS₂ (330 GPa·nm)⁴⁷, but larger than that of phosphorene (23.0 GPa·nm along armchair and 92.3 GPa nm along zigzag direction),48 demonstrating they are flexible materials. The corresponding Poisson's ratios v, defined as $v_x^{2D} = C_{12}/C_{22}$; $v_y^{2D} = C_{12}/C_{11}$, is found to be negative for PdB₄ due to the negative C₁₂, indicating it is an auxetic material.

Next, we explore the mechanical properties of PdB₄ monolayer under uniaxial strain. Generally, the strain disturbs the equilibrium state of the structure, thus the total energy of the system will rise (see strain-energy curve in Fig. S10). To provide an overall picture, the resultant strains (including both in-plane and vertical directions) in response to uniaxial deformation ranging from -8% to 8% is plotted by using a rectangular unit cell (Fig. S8a). We notice that our conclusions will not be changed when a primitive cell was used (Fig. S11). From Fig. 4b and 4d, one can see that the layer thickness (strain along z) decreases with the increase of the in-plane strain (along x and y), indicating the out-of-plane Poisson's ratios in PdB₄ sheet are always positive. To explore the in-plane Poisson's ratios, we consider uniaxial deformation of the sheet along x and monitor the change along y. Figure 4a shows that a nonlinear behavior is observed. By fitting the data to the function $y = -v_1x + v_2x^2 + v_3x^3$, with v_1 defined as the linear Poisson's ratio, we found the value of v_1 is -0.016, which confirms a negative in-plane Poisson's ratio in the x direction. This means that a PdB₄ sheet will expand (contract) along y when it is stretched (compressed) along x, corresponding to the auxetic behavior.

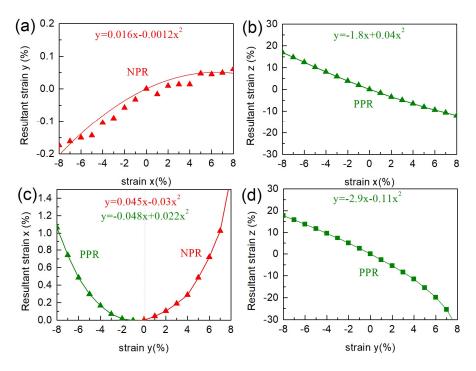


Figure 4. Mechanical response of PdB₄ monolayer under uniaxial strain along (a-b) x- and (c-d) y-directions. In the calculation, a rectangular cell was used. Data are fitted to the function $y = -v_1x + v_2x^2 + v_3x^3$.

Remarkably, the in-plane Poisson's ratio in the y direction shows a distinct behavior. Under tensile strain along y, the lateral dimension along x will expand, as indicated by the red data points in Fig. 4c. This gives a negative Poisson's ratio. The fitted v_1 is -0.045, which is comparable to the reported auxetic materials, such as single-layer black phosphorus

 $(-0.027)^{16}$, borophane (-0.053),²⁶ Be₅C₂ monolayer $(-0.041)^{18}$ and penta-graphene $(-0.068)^{17}$. Normally, an auxetic material would contract under a compressive strain, i.e., the Poisson's ratio maintains the same sign for negative strain (although its absolute value may change). Surprisingly, for PdB₄, under a compressive *y*-strain, the lattice size along *x* displays a response opposite to our expectation, i.e. an increasing trend, indicating a positive Poisson's ratio (v_1 =0.048) for this case (as indicated by the olive data points in Fig. 4c). In other words, the Poisson's ratio has a sign change at the equilibrium, between positive and negative strains along y direction. We call this behavior the half-auxetic effect. With this effect, PdB₄ exhibits the peculiar behavior that it always expands along *x* whenever it is strained along *y*, regardless of whether this strain is tensile or compressive.

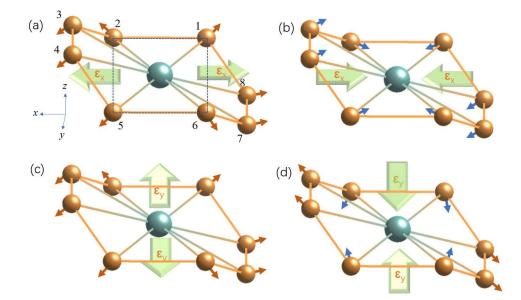


Figure 5. The structural evolution of the Pd-B₈ wheel of PdB₄ monolayer under uniaxial tensile/compressive strain along (a-b) x and (c-d) y direction, respectively. Transparent green arrows represent strain directions. Solid orange/blue arrows display the atoms move outward/inward. Atom 1, 2, 5 and 6 are within the *x*-*y* (*z*=0) plane (blue dashed frame).

Origin of the auxetic properties of PdB₄ **monolayer.** The auxetic properties of PdB₄ monolayer are intimately connected with the hypercoordinated Pd-B₈ wheel motif in its structure. As shown in Fig. 1, the Pd-B₈ wheel has an intrinsic out-of-plane buckling. To visualize this feature more clearly, we plot an enlarged view of the Pd-B₈ wheel in Fig. 5. Here, the Pd atom and B atoms labeled 1, 2, 5, and 6 are within the same 2D *x-y* plane (referred to as the *z*=0 plane), B 3 and 4 are above this plane, whereas B 7 and 8 are below the plane. First, consider the uniaxial strain applied along the *x* direction, for which the movement of the atoms is illustrated in Fig. 5a. One observes that when the wheel is stretched along *x*, the four out-of-plane B atoms will naturally move towards the *z*=0 plane. This movement will push out B 1, 2, 5 and 6 along *y*, because the bond lengths between the B sites

should be kept more or less unchanged due to the strong interatomic forces. Conversely, when the wheel is compressed along x (Fig. 5b), the four out-of-plane B will move further away from the z=0 plane, and the four in-plane B will then shift towards Pd. This explains the observed auxetic behavior for strains along x. Under a tensile strain along y direction (Fig. 5c), on the other hand, the four in-plane B atoms are stretched away from the center of the wheel. Due to the bonding between B sites, the four out-of-plane B move towards the z=0plane, i.e., the thickness of the sheet naturally shrinks due to the in-plane stretch. Meanwhile, these out-of-plane B also have strong bonding with the central Pd, which maintains a more or less unchanged bond length (between Pd and B 3, 4, 7, 8) in this process. This leads to the observed expansion along x. Note that the reduction of thickness in this case is remarkably high, e.g. it reaches more than 30% under +8% strain along y. This explains the observed sizable negative Poisson's ratio. Finally, consider the compressive strain along y. The in-plane B 1, 2, 5 and 6 are moved inward under strain (see Fig. 5d). For the out-of-plane B 3, 4, 7, and 8, under the joint forces from the in-plane B and Pd, their natural choices are (1) move further away from the z=0 plane and (2) move outward along x. From our above discussion, the movement (1) may lead to a shrink along x, but it turns out that this tendency is subdominant here and is surpassed by the movement (2). This results in the observed positive Poisson's ratio for compressive strains along y. From the above analysis, it is clear that the unusual half-auxetic effect in PdB₄ is a consequence of the special hypercoordinated Pd-B₈ wheel structure.

CONCLUSION

Our study of the 2D palladium borides provides a concrete example for exploring transition-metal borides as promising material systems with distinct properties. By searching for low-energy 2D Pd-B compounds, we identified three monolayers, namely one PdB₄ and two PdB₂ sheet possessing high chemical, dynamical and mechanical stabilities. In particular, single-layer PdB₄ consisting of buckled Pd-B₈ wheels is a hypercoordinated structure. Arising from its unique structural configuration, PdB₄ sheet exhibits a novel auxetic property, in which a NPR to PPR transition can be found when changing the sign of strain. Such a half-auxetic feature has not yet been reported in 2D materials. Additionally, the PdB₄ monolayer show high carrier motilities and the band gap of PdB₄ sheet is highly tunable by the strain effect. The fascinating properties, including half-auxeticity, ultrahigh mobilities and strain-sensitive bandgaps make PdB₄ monolayer an ideal integrated platform for nanoscale device applications.

ASSOCIATED CONTENT

Supporting Information

The Supporting Information is available free of charge.

Supplementary results including computational details of this work, the phonon spectrum, AIMD simulations, elastic constants and structural information for all predicted structures, band structures, PDOS, partial charge density distributions and light absorbance for the PdB₂ monolayers, electronic property and elastic energy of PdB₄ monolayer under strain effect.

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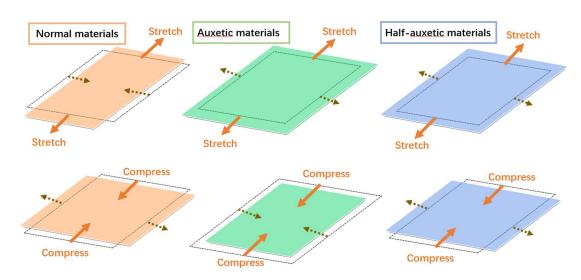


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